

ABSTRACT OF THE DISCLOSURE

The disclosure is provided with: a temporary crimping step in which one or more semiconductor chips 10 are sequentially laminated while being temporarily crimped in each of two or more locations on a substrate 30 to thereby form chip stacks ST in a temporarily crimped state; and a permanent crimping step in which the top surfaces of all of the chip stacks ST formed in the temporarily crimped state are sequentially heated, pressurized, and permanently crimped. Furthermore, a specifying step is provided prior to the temporary crimping step for specifying a separation distance Dd which is the distance from the chip stacks ST under permanent crimping to a location at which the temperature of the substrate 30, the temperature having been raised by heating for the permanent crimping, becomes less than or equal to a prescribed permissible temperature Td, and in the temporary crimping step, the chip stacks ST in the temporarily crimped state are formed separated from each other by the separation distance Dd or more.

FIGURE 7